



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C (Note 9)
60V	8mΩ @ V _{GS} = 10V	80A
	12mΩ @ V _{GS} = 4.5V	79A

Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ and yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and Loadswitch.

- Notebook Battery Power Management
- DC-DC Converters
- Loadswitch

Features

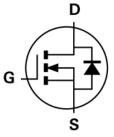
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

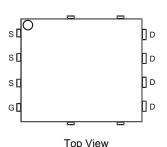
- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Top View Bottom View



Internal Schematic



Pin Configuration

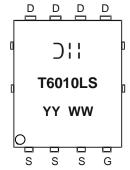
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMT6010LPS-13	PowerDI5060-8	2,500 / Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T6010LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	13.5 11	А
Continuous Drain Current (Note 6)	$T_C = +25^{\circ}C$ (Note 9) $T_C = +70^{\circ}C$	I _D	80 77	А
Maximum Continuous Body Diode Forward Current (Note 6)		I _S	80	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	125	Α
Avalanche Current, L=0.1mH		I _{AS}	20	Α
Avalanche Energy, L=0.1mH		E _{AS}	20	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	57	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		P_{D}	113	W
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	1.1	°C/W
Operating and Storage Temperature Range		$T_{J_{i}}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

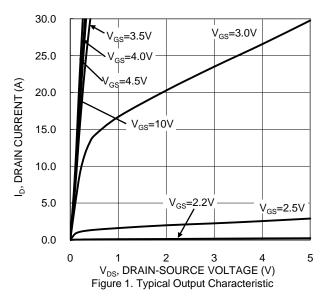
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	•					•	
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	6	8	~ 0	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	8	12	mΩ	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	-	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)	•					•	
Input Capacitance	C _{iss}	-	2090	-			
Output Capacitance	Coss	-	746	-	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	-	38.5	-		I = IIVIDZ	
Gate Resistance	Rg	-	0.59	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	19.3	-			
Total Gate Charge (V _{GS} = 10V)	Qq	-	41.3	-	nC	$V_{DS} = 30V, I_D = 20A$	
Gate-Source Charge	Q _{qs}	-	6.0	-	nc		
Gate-Drain Charge	Q _{gd}	-	8.8	-			
Turn-On Delay Time	t _{D(ON)}	-	5.7	-		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 3\Omega$	
Turn-On Rise Time	t _R	-	4.3	-			
Turn-Off Delay Time	t _{D(OFF)}	-	23.4	-	ns		
Turn-Off Fall Time	t _F	-	9.7	-			
Body Diode Reverse Recovery Time	t _{RR}	-	35.4	-	ns	1 004 11/14 4004/	
Body Diode Reverse Recovery Charge	Q _{RR}	-	38.2	-	nC	$I_F = 20A$, di/dt = 100A/ μ s	

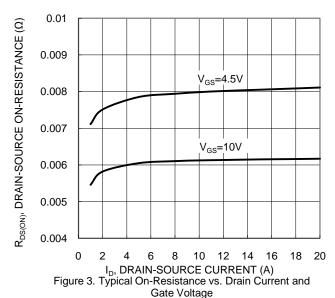
Notes:

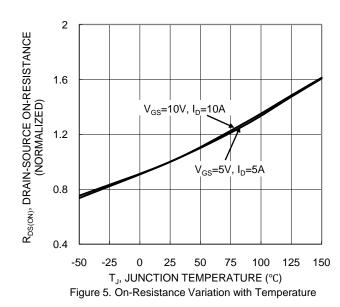
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 7. Short duration pulse test used to minimize self-heating effect.
- Guaranteed by design. Not subject to product testing.
 Package limited.

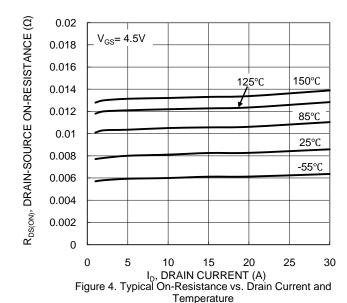












0.02 $R_{\mathrm{DS}(\text{ON})},$ DRAIN-SOURCE ON-RESISTANCE (Ω) 0.018 0.016 0.014 0.012 $V_{GS}=5V$, $I_D=5A$ 0.01 0.008 $V_{GS}=10V$, $I_{D}=10A$ 0.006 0.004 0.002 0 25 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



DMT6010LPS

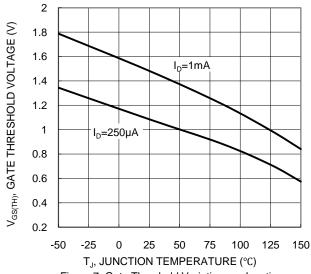
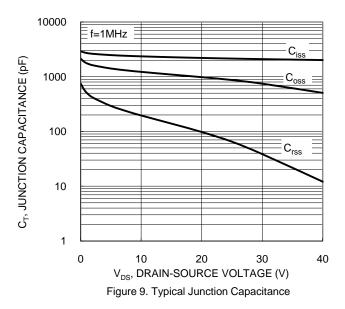
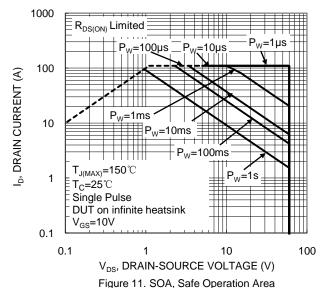
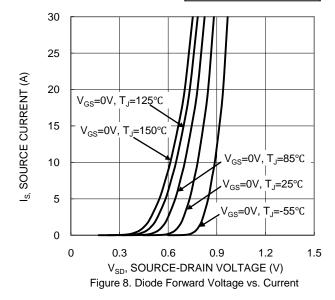
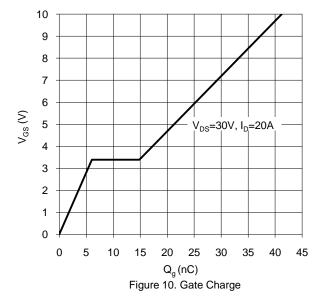


Figure 7. Gate Threshold Variation vs. Junction Temperature

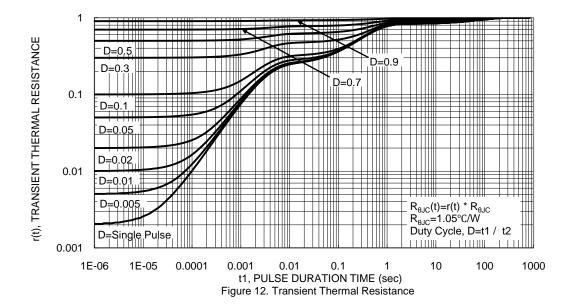








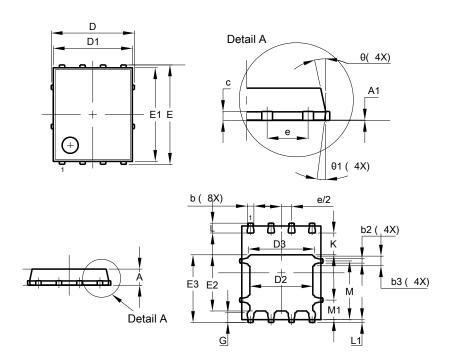






Package Outline Dimensions

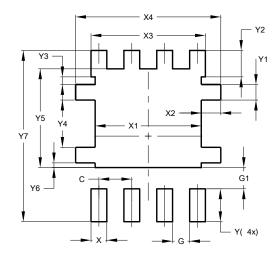
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	Į	5.15 BSC	,		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
θ	10°	12º	11º		
θ1	6º	80	7º		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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